

INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Complete if Known 10/574512	
				Application Number	New Application
				Filing Date	April 3, 2006
				First Named Inventor	MASSELINK et al
				Group Art Unit	2815
				Examiner Name	Ho, Anthony
				Confirmation No.	
Sheet	1	of	3	Attorney Docket Number	3367-102

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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published		T ²
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/A.H./	7.	W. T. Masselink, and Martin Zachau: "In _{0.35} Ga _{0.65} P light-emitting diodes grown by gas-source molecular beam epitaxy", Appl. Phys. Lett. 61, 58-60 (1992)		
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Examiner Signature	/Anthony Ho/	Date Considered	08/21/2007
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